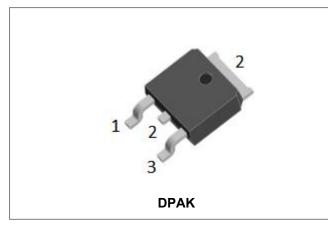


## MBRD660

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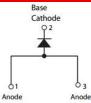
# **MBRD660 SCHOTTKY RECTIFIER**



#### Features

- 150℃ T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- "-A" is an AEC-Q101 qualified device
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### **Circuit Diagram**



### Applications

- Disk drives
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery charging

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	60	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=85°C, rectangular wave form	6	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse	125	А

## **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 6A, Pulse, T <sub>J</sub> = 25 °C	0.70	0.75	V
	V <sub>F2</sub>	@ 6A, Pulse, T <sub>J</sub> = 125 °C	0.60	0.70	V
Reverse Current *	I <sub>R1</sub>	$@V_R$ = rated $V_R$ , $T_J$ = 25 °C	0.01	1	mA
	I <sub>R2</sub>	$@V_R$ = rated $V_R$ , $T_J$ = 125 °C	3	10	mA
Junction Capacitance	Ст	@V <sub>R</sub> = 5.0V, T <sub>C</sub> = 25 °C f <sub>SIG</sub> = 1MHz	300	400	pF

\* Pulse width < 300  $\mu$ s, duty cycle < 2%

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## **MBRD660**



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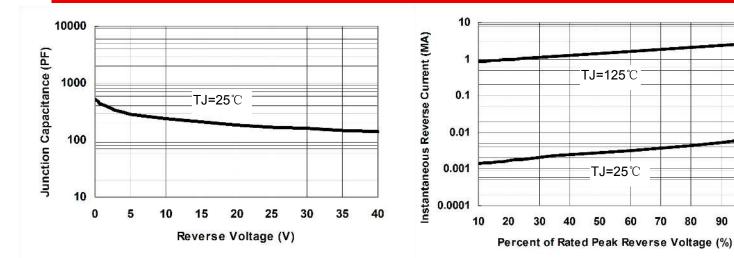
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## **Thermal-Mechanical Specifications:**

**Ratings and Characteristics Curves** 

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>θJC</sub>	-	6	°C/W
Approximate Weight	wt	-	0.39	g
Case Style		DPAK		







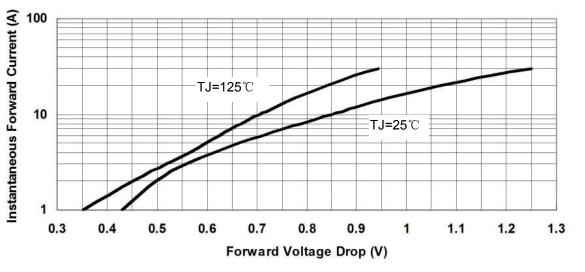


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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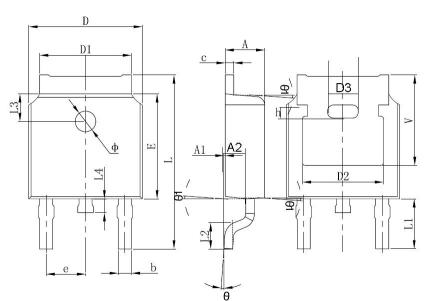
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**Technical Data** 

## **MBRD660**

### RoHS Po

### **Mechanical Dimensions DPAK**



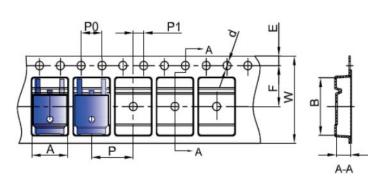
CYMBOL	Millim	neters	Inc	hes
SYMBOL	Min.	Max.	Min.	Max.
A	2.20	2.40	0.087	0.094
A1	0.00	0.127	0.000	0.005
b	0.66	0.86	0.026	0.034
с	0.46	0.60	0.018	0.024
D	6.50	6.70	0.256	0.264
D1	5.13	5.46	0.202	0.215
D2	4.83	REF.	0.190	REF.
E	6.00	6.20	0.236	0.244
е	2.186	2.386	0.086	0.094
L	9.70	10.40	0.381	0.409
L1	2.90	REF.	0.144	REF.
L2	1.40	1.70	0.055	0.067
L3	1.60	REF.	0.063	REF.
L4	0.60	1.00	0.024	0.039
Φ	1.10	1.30	0.043	0.051
Θ	0°	8°	0°	8°
h	0.00	0.30	0.000	0.012
V	5.35	REF.	0.211	REF.

## **Ordering Information**

Device	Package	Shipping
MBRD660	DPAK (Pb-Free)	2500pcs / reel
MBRD660TR	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

### **Carrier Tape & Reel Specification DPAK**



	Milli	SYMPOL Millimeters		
SYMBOL	Min.	Max.		
Α	6.80	7.00		
В	10.40	10.60		
С	2.60	2.80		
d	Φ1.45	Φ1.65		
E	1.65	1.85		
F	7.40	7.60		
P0	3.90	4.10		
Р	7.90	8.10		
P1	1.90	2.10		
W	15.90	16.30		

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## **Marking Diagram**



#### Where XXXXX is YYWWL

MBRD660 = Part Name = SSG SSG YΥ = Year WW = Week = Lot Number

L

Cautions: Molding resin Epoxy resin UL:94V-0



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